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#### 1. Global joint venture starts operations as WeEn Semiconductors

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Thank you for your cooperation and understanding,

WeEn Semiconductors



Product data sheet

## 1. General description

Planar passivated high commutation three quadrant triac in a SOT404 (D2PAK) surface mountable plastic package. This "series ET" triac balances the requirements of commutation performance and gate sensitivity and is intended for interfacing with low power drivers including microcontrollers. It is used in applications where "high junction operating temperature" capability is required.

#### 2. Features and benefits

- 3Q technology for improved noise immunity
- Direct interfacing with low power drivers and microcontrollers
- Good immunity to false turn-on by dV/dt
- High commutation capability with sensitive gate
- High junction operating temperature capability
- High voltage capability
- Planar passivated for voltage ruggedness and reliability
- Sensitive gate for easy logic level triggering
- Surface mountable package
- · Triggering in three quadrants only

## 3. Applications

- Applications subject to high temperature
- Electronic thermostats (heating and cooling)
- · High power motor controls e.g. washing machines and vacuum cleaners
- Refrigeration and air-conditioner compressor controls

#### 4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$V_{DRM}$	repetitive peak off- state voltage		-	-	800	V
I <sub>TSM</sub>	non-repetitive peak on- state current	full sine wave; $T_{j(init)} = 25 ^{\circ}C$ ; $t_p = 20  \text{ms}$ ; Fig. 4; Fig. 5	-	-	100	А
Tj	junction temperature		-	-	150	°C
I <sub>T(RMS)</sub>	RMS on-state current	full sine wave; $T_{mb} \le 125 ^{\circ}\text{C}$ ; Fig. 2; Fig. 3	-	-	12	А





Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Static characteristics							
I <sub>GT</sub>	gate trigger current	$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T2+ G+;$ $T_j = 25 \text{ °C}; Fig. 7$		-	-	10	mA
		$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T2+ \text{ G-};$ $T_j = 25 \text{ °C}; Fig. 7$		-	-	10	mA
		$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T2- \text{ G-};$ $T_j = 25 \text{ °C}; Fig. 7$		-	-	10	mA

# 5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	T1	main terminal 1	mb	T2—T1
2	T2	main terminal 2		G sym051
3	G	gate		<b>.</b>
mb	T2	mounting base; main terminal 2	1 3	
			D2PAK (SOT404)	

# 6. Ordering information

Table 3. Ordering information

Type number	Package					
	Name	Description	Version			
BTA312B-800ET	D2PAK	plastic single-ended surface-mounted package (D2PAK); 3 leads (one lead cropped)	SOT404			

### 7. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
$V_{DRM}$	repetitive peak off-state voltage		-	800	V
I <sub>T(RMS)</sub>	RMS on-state current	full sine wave; $T_{mb} \le 125 ^{\circ}\text{C}$ ; Fig. 2; Fig. 3	-	12	Α
I <sub>TSM</sub>	non-repetitive peak on-state current	full sine wave; $T_{j(init)} = 25 ^{\circ}C$ ; $t_p = 20  \text{ms}$ ; Fig. 4; Fig. 5	-	100	Α
		full sine wave; $T_{j(init)} = 25 ^{\circ}C$ ; $t_p = 16.7  \text{ms}$	-	110	А
l <sup>2</sup> t	I <sup>2</sup> t for fusing	t <sub>p</sub> = 10 ms; SIN	-	50	A <sup>2</sup> s
dI <sub>T</sub> /dt	rate of rise of on-state current	$I_T = 20 \text{ A}; I_G = 0.2 \text{ A}; dI_G/dt = 0.2 \text{ A/}\mu\text{s}$	-	100	A/µs
I <sub>GM</sub>	peak gate current		-	2	Α
$P_{GM}$	peak gate power		-	5	W
$P_{G(AV)}$	average gate power	over any 20 ms period	-	0.5	W
T <sub>stg</sub>	storage temperature		-40	150	°C
T <sub>j</sub>	junction temperature		-	150	°C

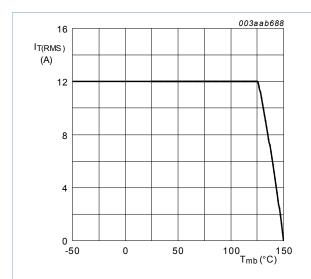
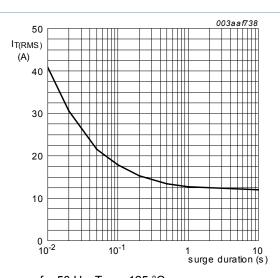


Fig. 1. RMS on-state current as a function of mounting base temperature; maximum values



f = 50 Hz; T<sub>mb</sub> = 125 °C

Fig. 2. RMS on-state current as a function of surge duration; maximum values

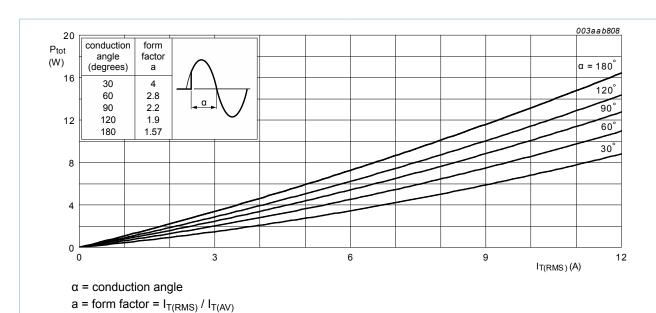


Fig. 3. Total power dissipation as a function of RMS on-state current; maximum values

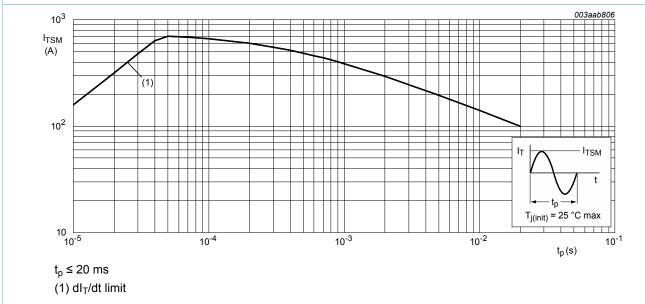


Fig. 4. Non-repetitive peak on-state current as a function of pulse duration; maximum values

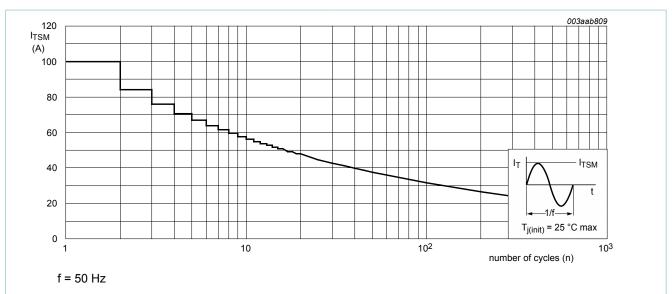


Fig. 5. Non-repetitive peak on-state current as a function of the number of sinusoidal current cycles; maximum values

### 8. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R <sub>th(j-mb)</sub>	thermal resistance from junction to mounting base	full cycle; Fig. 6	-	-	1.5	K/W
		half cycle; Fig. 6	-	-	2	K/W
R <sub>th(j-a)</sub>	thermal resistance from junction to ambient	printed circuit board mounted; minimum footprint	-	55	-	K/W

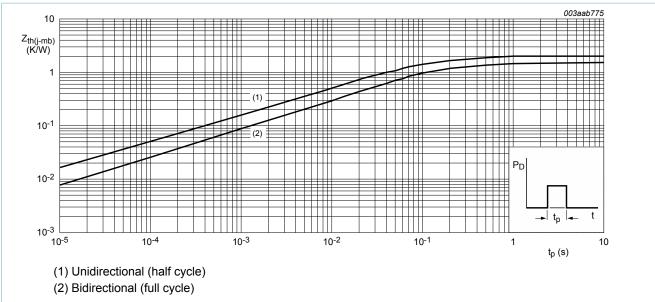
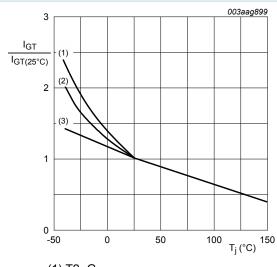


Fig. 6. Transient thermal impedance from junction to mounting base as a function of pulse duration

### 9. Characteristics

Table 6. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	acteristics		'			
I <sub>GT</sub>	gate trigger current	$V_D = 12 \text{ V; } I_T = 0.1 \text{ A; } T2+ G+;$ $T_j = 25 \text{ °C; } Fig. 7$	-	-	10	mA
		$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T2+ \text{ G-};$ $T_j = 25 ^{\circ}\text{C}; \underline{\text{Fig. 7}}$	-	-	10	mA
		$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T2- \text{G-};$ $T_j = 25 \text{ °C}; Fig. 7$	-	-	10	mA
I <sub>L</sub>	latching current	$V_D = 12 \text{ V}; I_G = 0.1 \text{ A}; T2+ G+;$ $T_j = 25 \text{ °C}; Fig. 8$	-	-	25	mA
		$V_D = 12 \text{ V}; I_G = 0.1 \text{ A}; T2+ G-;$ $T_j = 25 \text{ °C}; Fig. 8$	-	-	30	mA
		$V_D = 12 \text{ V}; I_G = 0.1 \text{ A}; \text{ T2- G-};$ $T_j = 25 ^{\circ}\text{C}; \text{ Fig. 8}$	-	-	25	mA
I <sub>H</sub>	holding current	V <sub>D</sub> = 12 V; T <sub>j</sub> = 25 °C; <u>Fig. 9</u>	-	-	15	mA
V <sub>T</sub>	on-state voltage	I <sub>T</sub> = 15 A; T <sub>j</sub> = 25 °C; <u>Fig. 10</u>	-	1.3	1.6	V
V <sub>GT</sub>	gate trigger voltage	$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T_j = 25 \text{ °C};$ Fig. 11	-	0.7	1	V
		V <sub>D</sub> = 400 V; I <sub>T</sub> = 0.1 A; T <sub>j</sub> = 150 °C; Fig. 11	0.25	0.4	-	V
I <sub>D</sub>	off-state current	V <sub>D</sub> = 800 V; T <sub>j</sub> = 150 °C	-	0.4	2	mA
Dynamic ch	naracteristics	1				
dV <sub>D</sub> /dt	rate of rise of off-state voltage	$V_{DM}$ = 536 V; $T_j$ = 150 °C; ( $V_{DM}$ = 67% of $V_{DRM}$ ); exponential waveform; gate open circuit	30	-	-	V/µs
dl <sub>com</sub> /dt	rate of change of commutating current	$V_D$ = 400 V; $T_j$ = 150 °C; $I_{T(RMS)}$ = 12 A; $dV_{com}/dt$ = 20 V/ $\mu$ s; (without snubber condition); gate open circuit	2	-	-	A/ms
		$V_D$ = 400 V; $T_j$ = 150 °C; $I_{T(RMS)}$ = 12 A; $dV_{com}/dt$ = 10 V/ $\mu$ s; gate open circuit	3.5	-	-	A/ms
		$V_D$ = 400 V; $T_j$ = 150 °C; $I_{T(RMS)}$ = 12 A; $dV_{com}/dt$ = 1 V/µs; gate open circuit	5	-	-	A/ms



- (1) T2- G-
- (2) T2+ G-
- (3) T2+ G+

Fig. 7. Normalized gate trigger current as a function of junction temperature

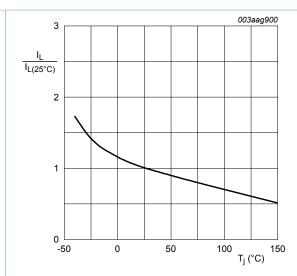


Fig. 8. Normalized latching current as a function of junction temperature

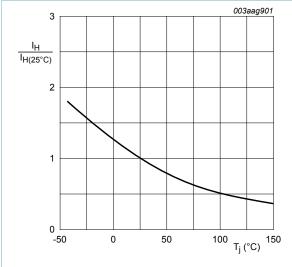
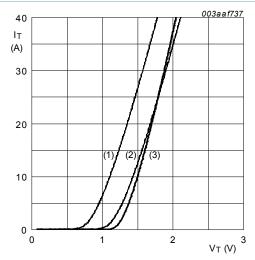


Fig. 9. Normalized holding current as a function of junction temperature



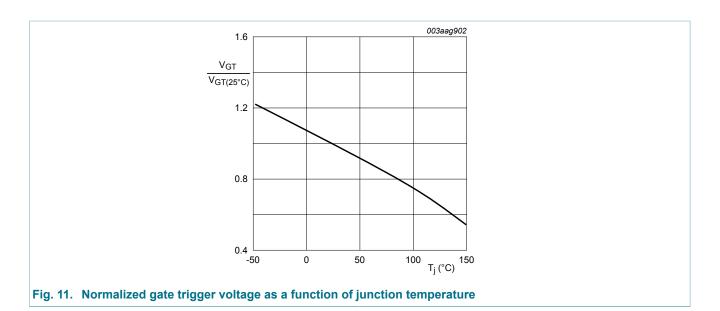
 $V_o$  = 1.127 V;  $R_s$  = 0.27  $\Omega$ 

(1) T<sub>i</sub> = 150 °C; typical values

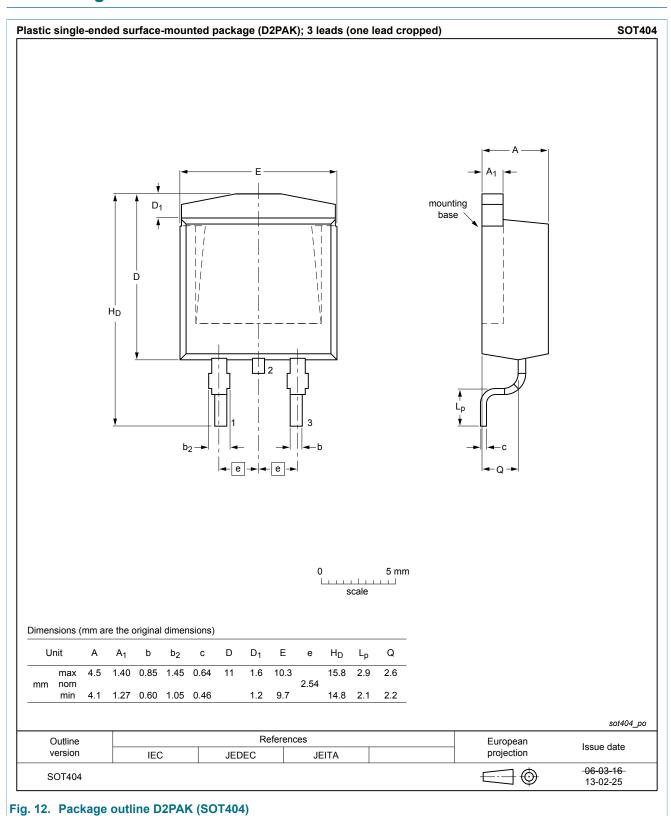
(2) T<sub>i</sub> = 150 °C; maximum values

(3) T<sub>i</sub> = 25 °C; maximum values

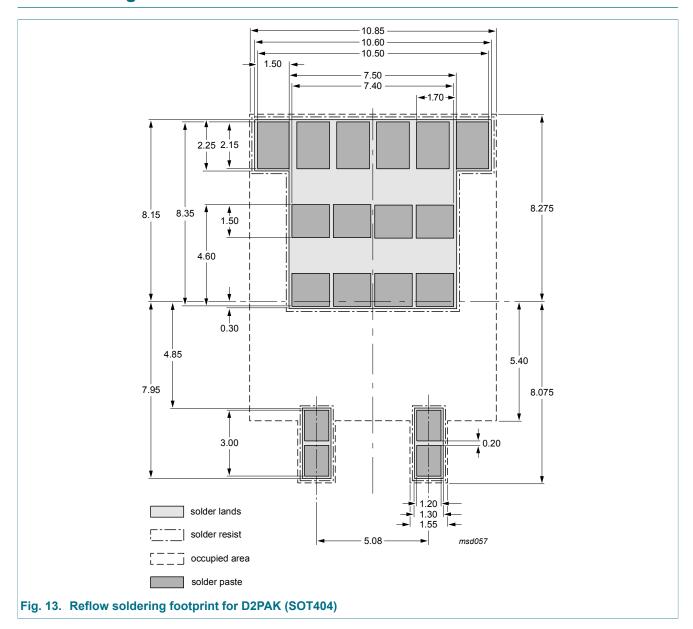
Fig. 10. On-state current as a function of on-state voltage



# 10. Package outline



# 11. Soldering



#### 12. Legal information

#### 12.1 Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
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- Please consult the most recently issued document before initiating or completing a design.
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